Microsemi
POWER PRODUCTS GROUP

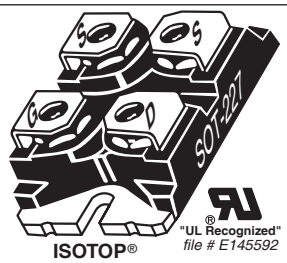
Power MOS 8 Cooler!™

# APT19F100J

**1000V, 19A, 0.46Ω Max, $t_{rr}$ ≤270ns**

## N-Channel FREDFET

Power MOS 8™ is a high speed, high voltage N-channel switch-mode power MOSFET. This 'FREDFET' version has a drain-source (body) diode that has been optimized for high reliability in ZVS phase shifted bridge and other circuits through reduced $t_{rr}$, soft recovery, and high recovery dv/dt capability. Low gate charge, high gain, and a greatly reduced ratio of $C_{rss}/C_{iss}$ result in excellent niose immunity and low switching loss. The intrinsic gate resistance and capacitance of the poly-silicon gate structure help control di/dt during switching, resulting in low EMI and reliable paralleling, even when switching at very high frequency.




"UL Recognized" file # E145592

ISOTOP®
APT19F100J

Single die FREDFET


## FEATURES

- **Fast switching with low EMI**
- **Low $t_{rr}$ for high reliability**
- **Ultra low $C_{rss}$ for improved noise immunity**
- **Low gate charge**
- **Avalanche energy rated**
- **RoHS compliant**

## TYPICAL APPLICATIONS

- **ZVS phase shifted and other full full bridge**
- **Half bridge**
- **PFC and other boost converter**
- **Buck converter**
- **Single and two switch forward**
- **Flyback**

### Absolute Maximum Ratings

| Symbol | Parameter | Ratings | Unit |
|---|---|---|---|
| $I_D$ | Continuous Drain Current @ $T_C$ = 25°C | 19 | A |
| | Continuous Drain Current @ $T_C$ = 100°C | 12 | |
| $I_{DM}$ | Pulsed Drain Current ① | 120 | |
| $V_{GS}$ | Gate-Source Voltage | ±30 | V |
| $E_{AS}$ | Single Pulse Avalanche Energy ② | 1875 | mJ |
| $I_{AR}$ | Avalanche Current, Repetitive or Non-Repetitive | 16 | A |

### Thermal and Mechanical Characteristics

| Symbol | Characteristic | Min | Typ | Max | Unit |
|---|---|---|---|---|---|
| $P_D$ | Total Power Dissipation @ $T_C$ = 25°C | | | 460 | W |
| $R_{\theta JC}$ | Junction to Case Thermal Resistance | | | 0.27 | °C/W |
| $R_{\theta CS}$ | Case to Sink Thermal Resistance, Flat, Greased Surface | | 0.15 | | |
| $T_J$,$T_{STG}$ | Operating and Storage Junction Temperature Range | -55 | | 150 | °C |
| $V_{Isolation}$ | RMS Voltage (50-60hHz Sinusoidal Wavefomr Ffrom Terminals to Mounting Base for 1 Min.) | 2500 | | | V |
| $W_T$ | Package Weight | | 1.03 | | oz |
| | | | 29.2 | | g |
| Torque | Terminals and Mounting Screws. | | | 10 | in·lbf |
| | | | | 1.1 | N·m |



050-8080 Rev A 9-2006

## Static Characteristics $T_J = 25°C$ unless otherwise specified APT29F100B2_L

| Symbol | Parameter | Test Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $V_{BR(DSS)}$ | Drain-Source Breakdown Voltage | $V_{GS}$ = 0V, $I_D$ = 250µA | | 1000 | | | V |
| $\Delta V_{BR(DSS)}/\Delta T_J$ | Breakdown Voltage Temperature Coefficient | Reference to 25°C, $I_D$ = 250µA | | | 1.15 | | V/°C |
| $R_{DS(on)}$ | Drain-Source On Resistance③ | $V_{GS}$ = 10V, $I_D$ = 16A | | | 0.39 | 0.46 | Ω |
| $V_{GS(th)}$ | Gate-Source Threshold Voltage | $V_{GS}$ = $V_{DS}$, $I_D$ = 2.5mA | | 3 | 4 | 5 | V |
| $\Delta V_{GS(th)}/\Delta T_J$ | Threshold Voltage Temperature Coefficient | | | | -10 | | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 1000V | $T_J$ = 25°C | | | 250 | µA |
| | | $V_{GS}$ = 0V | $T_J$ = 125°C | | | 1000 | |
| $I_{GSS}$ | Gate-Source Leakage Current | $V_{GS}$ = ±30V | | | | ±100 | nA |

## Dynamic Characteristics $T_J = 25°C$ unless otherwise specified

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| $g_{fs}$ | Forward Transconductance | $V_{DS}$ = 50V, $I_D$ = 16A | | 34 | | S |
| $C_{iss}$ | Input Capacitance | $V_{GS}$ = 0V, $V_{DS}$ = 25V f = 1MHz | | 8500 | | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | | 115 | | |
| $C_{oss}$ | Output Capacitance | | | 715 | | |
| $C_{o(cr)}$ ④ | Effective Output Capacitance, Charge Related | $V_{GS}$ = 0V, $V_{DS}$ = 0V to 667V | | 290 | | |
| $C_{o(er)}$ ⑤ | Effective Output Capacitance, Energy Related | | | 150 | | |
| $Q_g$ | Total Gate Charge | $V_{GS}$ = 0 to 10V, $I_D$ = 16A, $V_{DS}$ = 500V | | 260 | | nC |
| $Q_{gs}$ | Gate-Source Charge | | | 46 | | |
| $Q_{gd}$ | Gate-Drain Charge | | | 125 | | |
| $t_{d(on)}$ | Turn-On Delay Time | **Resistive Switching** $V_{DD}$ = 667V, $I_D$ = 16A $R_G$ = 2.2Ω⑥, $V_{GG}$ = 15V | | 39 | | ns |
| $t_r$ | Current Rise Time | | | 35 | | |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 130 | | |
| $t_f$ | Current Fall Time | | | 33 | | |

## Source-Drain Diode Characteristics

| Symbol | Parameter | Test Conditions | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| $I_S$ | Continuous Source Current (Body Diode) | MOSFET symbol showing the integral reverse p-n junction diode (body diode)   | | | | 100 | A |
| $I_{SM}$ | Pulsed Source Current (Body Diode)① | | | | | 120 | |
| $V_{SD}$ | Diode Forward Voltage | $I_{SD}$ = 16A, $T_J$ = 25°C, $V_{GS}$ = 0V | | | | 1.1 | V |
| $t_{rr}$ | Reverse Recovery Time | $I_{SD}$ = 16A③ $di_{SD}/dt$ = 100A/µs | $T_J$ = 25°C | | 230 | 270 | ns |
| | | | $T_J$ = 125°C | | 500 | 640 | |
| $Q_{rr}$ | Reverse Recovery Charge | | $T_J$ = 25°C | | 13 | | µC |
| | | | $T_J$ = 125°C | | 35 | | |
| $I_{rrm}$ | Reverse Recovery Current | | $T_J$ = 25°C | | 11 | | A |
| | | | $T_J$ = 125°C | | 15 | | |
| dv/dt | Peak Recovery dv/dt | $I_{SD}$ ≤ 16A, di/dt ≤1000A/µs, $V_{DD}$ = 667V, $T_J$ = 125°C | | | | 25 | V/ns |

① Repetitive Rating: Pulse width and case temperature limited by maximum junction temperature.

② Starting at $T_J$ = 25°C, L = 14.65mH, $R_G$ = 2.2Ω, $I_{AS}$ = 16A.

③ Pulse test: Pulse Width < 380µs, duty cycle < 2%.

④ $C_{o(cr)}$ is defined as a fixed capacitance with the same stored charge as $C_{OSS}$ with $V_{DS}$ = 67% of $V_{(BR)DSS}$.

⑤ $C_{o(er)}$ is defined as a fixed capacitance with the same stored energy as $C_{OSS}$ with $V_{DS}$ = 67% of $V_{(BR)DSS}$. To calculate $C_{o(cr)}$ for any value of $V_{DS}$ less than $V_{(BR)DSS,}$ use this equation: $C_{o(er)}$ = -2.47E-7/$V_{DS}$^2 + 4.36E-8/$V_{DS}$ + 8.44E-11.

⑥ $R_G$ is external gate resistance, not including internal gate resistance or gate driver impedance. (MIC4452)

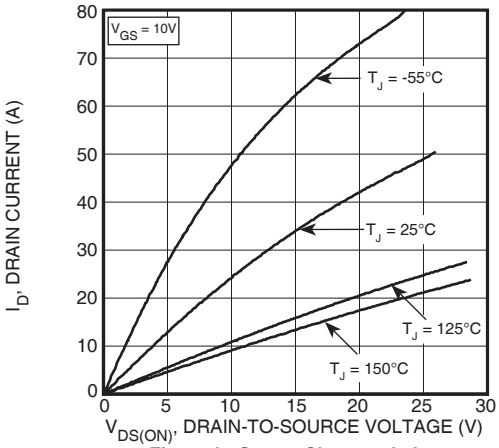



**Figure 1, Output Characteristics**

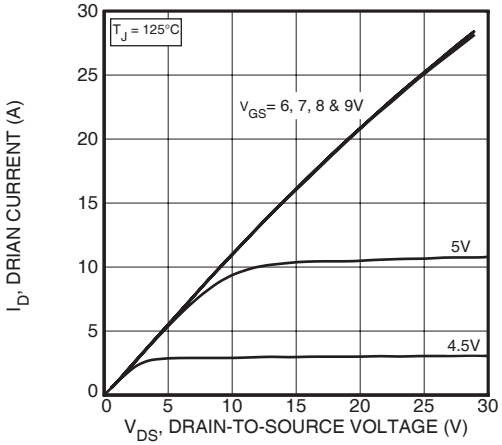



**Figure 2, Output Characteristics**

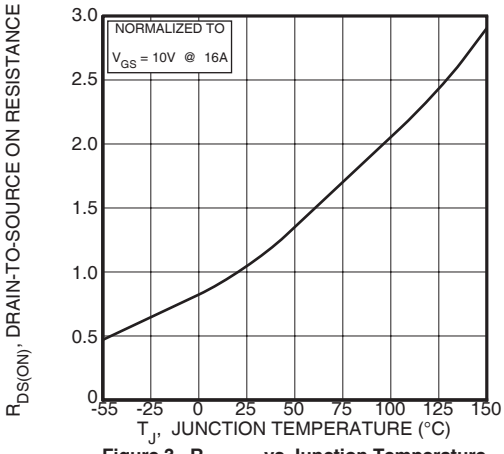



**Figure 3, $R_{DS(ON)}$ vs Junction Temperature**

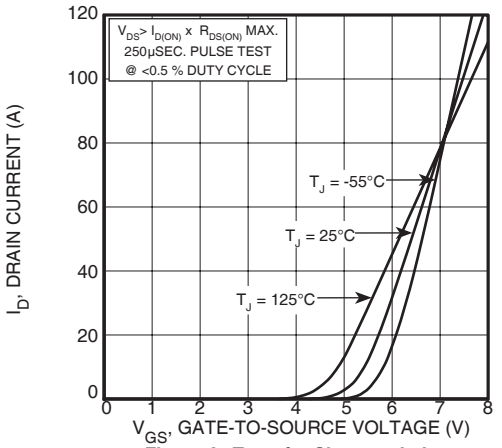



**Figure 4, Transfer Characteristics**

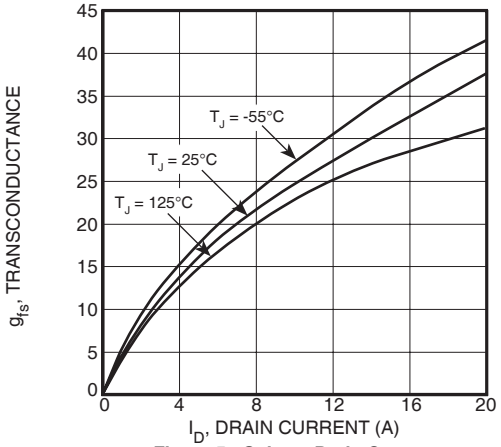



**Figure 5, Gain vs Drain Current**

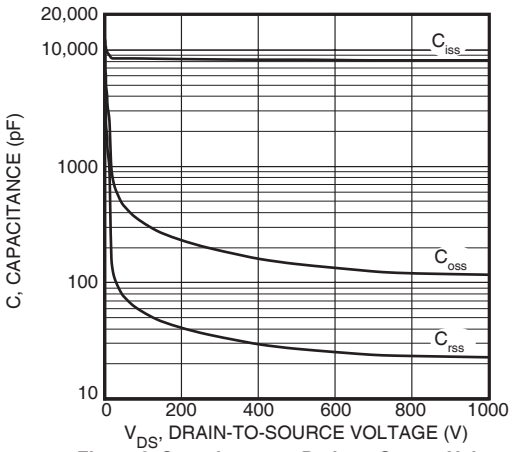



**Figure 6, Capacitance vs Drain-to-Source Voltage**

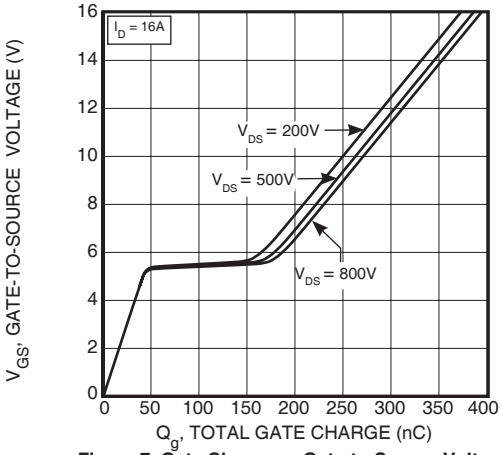



**Figure 7, Gate Charge vs Gate-to-Source Voltage**

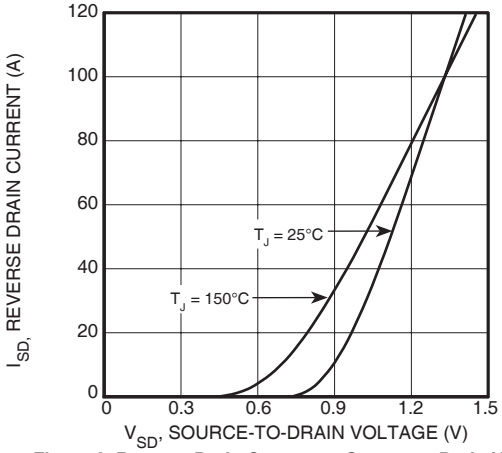



**Figure 8, Reverse Drain Current vs Source-to-Drain Voltage**

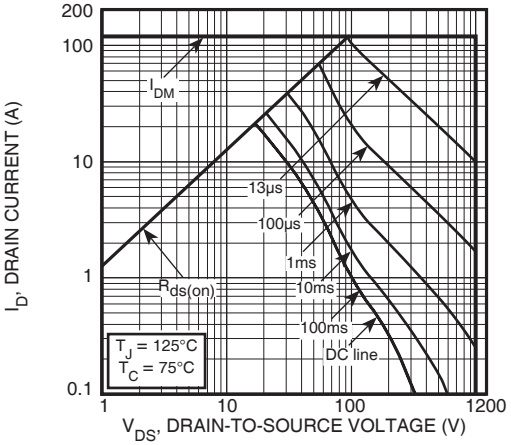



**Figure 9, Forward Safe Operating Area**

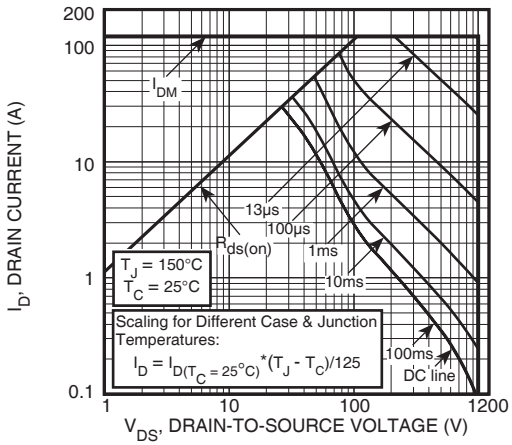



**Figure 10, Maximum Forward Safe Operating Area**

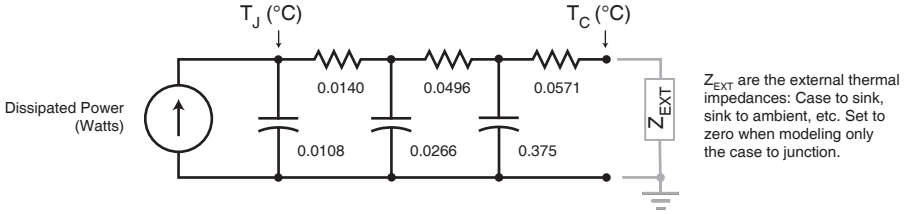



**Figure 11, Transient Thermal Impedance Model**

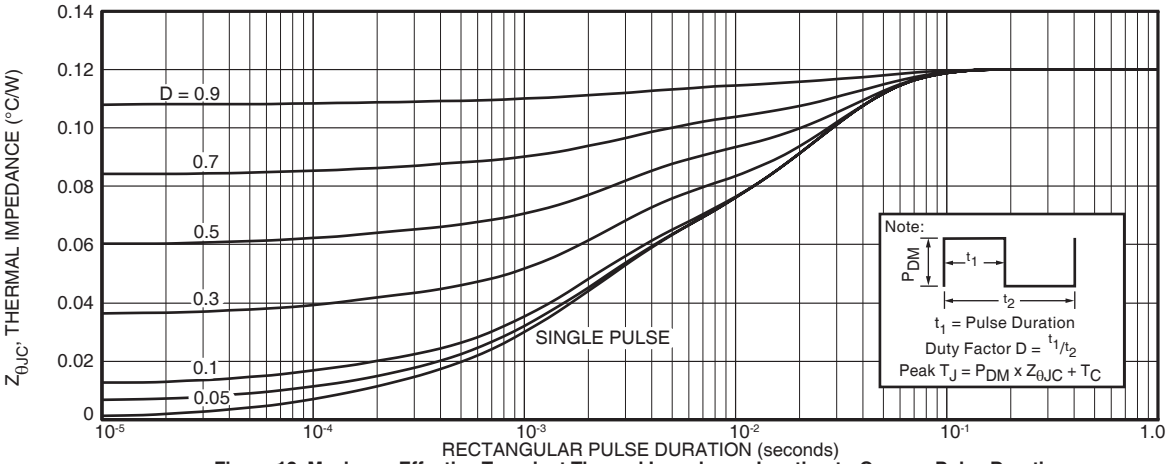
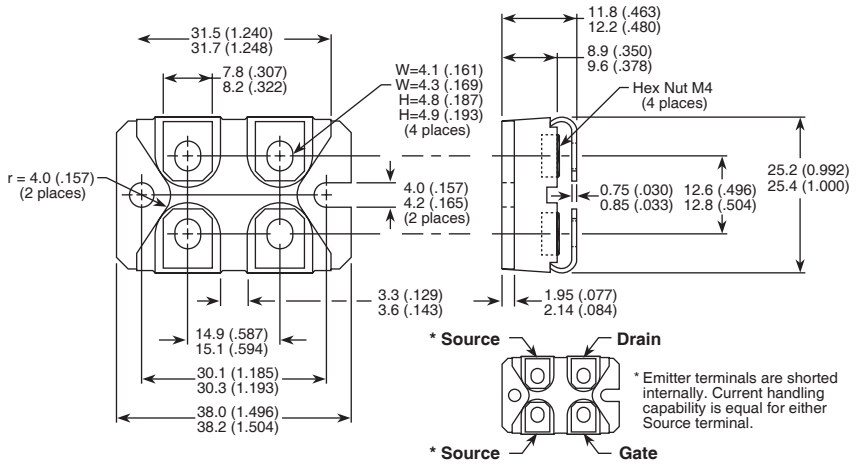



**Figure 12. Maximum Effective Transient Thermal Impedance Junction-to-Case vs Pulse Duration**

## SOT-227 (ISOTOP®) Package Outline




Dimensions in Millimeters and (Inches)